IN THE CLAIMS

What is claimed is:

1. A method comprising;

forming a cavity in a plating material;

attaching a die in the cavity;

forming a dielectric material adjacent the die;

forming vias in a region of the dielectric material adjacent the die;

forming PoP land areas within the vias;

forming PoP land structures in the PoP land areas;

forming vias in the die area to expose die pads on the die;

forming die pad interconnect structures in the die area vias and forming PoP interconnect structures in the dielectric region vias; and

removing the plating material to expose the die and the PoP land structures.

2. The method of claim 1 further comprising forming subsequent metal layers on the die pad interconnect structures and on the PoP interconnect structures to form a coreless substrate.

3. The method of claim 2 further comprising wherein the die is partially embedded into the coreless substrate, and wherein the dielectric material is formed along a portion of a sidewall of the die.

4. The method of claim 2 further comprising wherein the die is substantially fully embedded into the coreless substrate, and wherein the dielectric material is formed along a portion of a sidewall of the die.

5. The method of claim 1 further comprising wherein a portion of the dielectric material comprises a fillet structure surrounding a portion of the sidewall of the die.

6. The method of claim 5 further comprising wherein an angle is between a raised portion of the fillet structure and a planar top portion of the dielectric material.

7. The method of claim 2 further comprising wherein the PoP land structures comprise raised, electrolytically plated lands on top of the coreless package.

8. The method of claim 1 further comprising wherein interconnect structures

of a second package are attached to the PoP land structures.

9. A method comprising;

forming a cavity in a plating material to hold a die;

attaching the die in the cavity;

forming a dielectric material adjacent the die;

forming vias in the dielectric material adjacent the die;

forming PoP lands in the vias;

forming interconnects in the vias; and

removing the plating material to expose the PoP lands and die,

wherein the die is disposed above the PoP lands.

10. The method of claim 9 further comprising wherein the die is attached using an adhesive film.

11. The method of claim 9 further comprising wherein the plating material comprises an electroplating metal.

12. The method of claim 11 wherein forming the PoP lands in the vias further comprises forming wire bond pads in the vias.

13. The method of claim 9 further comprising wherein forming the PoP lands in the vias comprises using the plating material as the plating bus to form the PoP lands.

14. The method of claim 9 further comprising:

forming vias in a die area, exposing pads on the die; and

plating the vias in the die area.

15. The method of claim 14 further comprising wherein a coreless substrate is built up on the PoP lands and on the plated die vias.

16. A structure comprising:

a partially embedded die disposed in a coreless substrate; and

raised PoP lands adjacent the die on top of the coreless substrate,

wherein the PoP lands are capable of receiving a second substrate.

17. The structure of claim 16 further comprising an adhesive film disposed on a top surface of the die, and wherein the coreless substrate comprises a portion of a POP package structure.

18. The structure of claim 16 wherein the coreless substrate comprises a portion of a PoP package structure, and further wherein interconnect structures of a

second package are disposed on the the PoP lands of the coreless substrate.

19. The structure of claim 16 wherein the die comprises a dielectric filet structure surrounding the sidewall of the die.

20. The structure of claim 19 wherein there is an angle between a planar top portion of the dielectric material of the coreless substrate and the dielectric fillet structure.

21. The structure of claim 18 wherein a die of the second package is directly above the die of the coreless substrate

22. The structure of claim 16 wherein there is a distance between a top side of the die and a top side of the PoP land.

23. A structure comprising:

a die disposed in a coreless substrate, wherein at least a portion of the die is embedded in the coreless substrate;

raised PoP lands adjacent the die, wherein the PoP lands and the die are capable of receiving a second substrate;

a dielectric film adjacent the die, wherein die interconnect structures are disposed in the dielectric film and are connected to pads of the die;

PoP interconnect structures that are connected to the PoP lands; and

a first metal layer disposed on the PoP interconnect structures and on the die interconnect structures.

24. The structure of claim 23 wherein a portion of the dielectric material is adjacent a sidewall of the die and raised above a top side of the PoP lands.

25. The structure of claim 23 wherein the PoP lands comprise plated metal.

26. The structure of claim 23 wherein the structure comprises a portion of coreless package structure, wherein a second package is connected to the coreless package structure.

27. The structure of claim 26 wherein interconnect structures of the second package are connected to the PoP lands of the coreless package structure.

28. The structure of claim 24 wherein there is an angle between a top planar portion of the dielectric material of the coreless package and the dielectric material adjacent the sidewall of the die.

29. The structure of claim 23 wherein the die comprises a thickness of less than

about 150 microns.

30. The structure of claim 23 further comprising a system comprising:

a bus communicatively coupled to the structure; and

a DRAM communicatively coupled to the bus.

What is claimed is:

1. A structure, comprising:

a partially embedded die disposed in a coreless substrate, wherein the partially embedded die includes a top surface and a bottom/active surface;

wherein the coreless substrate includes a dielectric material having a planar top portion and having a fillet structure that is raised in relation to the dielectric material planar top portion, wherein the fillet structure of the dielectric material has a sloped portion extending from the planar top portion to a position adjacent the partially embedded die top surface without extending onto the partially embedded die top surface, and wherein the fillet structure is adjacent to a sidewall of the partially embedded die; and

raised PoP lands adjacent the partially embedded die on the dielectric material planar top portion of the coreless substrate, wherein the PoP lands are capable of receiving a second substrate.

2. The structure of claim 1 further comprising an adhesive film disposed on a top surface of the partially embedded die, and wherein the coreless substrate comprises a portion of a POP package structure.

3. The structure of claim 1 wherein the coreless substrate comprises a portion of a PoP package structure, and further wherein interconnect structures of a second package are disposed on the PoP lands of the coreless substrate.

4. The structure of claim 3 wherein a die of the second package is directly above the partially embedded die disposed in the coreless substrate.

5. The structure of claim 1 wherein there is a distance between a top side of the die and a top side of the PoP land.

6. A structure comprising:

a die disposed in a coreless substrate, wherein at least a portion of the die is embedded in the coreless substrate and wherein the die includes a top surface and a bottom/active surface;

wherein the coreless substrate includes a dielectric material having a planar top portion and having a fillet structure that is raised in relation to the dielectric material planar top portion, wherein the fillet structure of the dielectric material has a sloped portion extending from the planar top portion to a position adjacent the die top surface without extending onto the die top surface, and wherein the fillet structure is adjacent to a sidewall of die;

raised PoP lands adjacent the die on the dielectric material planar top portion of the coreless substrate, wherein the PoP lands and the die are capable of receiving a second substrate;

a dielectric film adjacent the die bottom/active surface, wherein die interconnect structures are disposed in the dielectric film and are connected to pads of the die bottom/active surface;

PoP interconnect structures that are connected to the PoP lands; and

a first metal layer disposed on the PoP interconnect structures and on the die interconnect structures.

7. The structure of claim 6 wherein the PoP lands comprise plated metal.

8. The structure of claim 6 wherein the coreless substrate comprises a portion of coreless package structure, wherein a second package is connected to the coreless package structure.

9. The structure of claim 8 wherein interconnect structures of the second package are connected to the PoP lands of the coreless package structure.

10. The structure of claim 6 wherein the die comprises a thickness of less than about 150 microns.

11. The structure of claim 6 further comprising a system comprising: a bus communicatively coupled to the structure; and a DRAM communicatively coupled to the bus.

12. A structure comprising:

a die having a thickness of less than about 150 microns disposed in a coreless substrate, wherein at least a portion of the die is embedded in the coreless substrate and wherein the die includes a top surface and a bottom/active surface;

wherein the coreless substrate includes a dielectric material having a planar top portion and having a fillet structure that is raised in relation to the dielectric material planar top portion, wherein the fillet structure of the dielectric material has a sloped portion extending from the planar top portion to a position adjacent the die top surface without extending onto the die top surface, and wherein the fillet structure is adjacent to a sidewall of the die;

raised PoP lands comprising a plated metal adjacent the die on the dielectric material planar top portion of the coreless substrate;

a dielectric film adjacent the die bottom/active surface, wherein die interconnect structures are disposed in the dielectric film and are connected to pads of the die bottom/active surface;

PoP interconnect structures that are connected to the PoP lands;

a first metal layer disposed on the PoP interconnect structures and on the die interconnect structures;

wherein the coreless substrate comprises a portion of coreless package structure; and

a second package connected to the coreless package structure, wherein the second package is connected to the PoP lands of the coreless package structure with PoP interconnect structure solder balls.